

## HIGH POWER NPN SILICON TRANSISTORS

- STMicroelectronics PREFERRED SALESTYPES
- NPN TRANSISTOR
- HIGH CURRENT CAPABILITY
- FAST SWITCHING SPEED
- VERY LOW SATURATION VOLTAGE AND HIGH GAIN

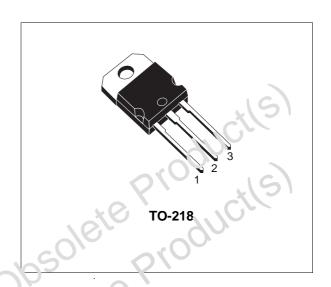
### **APPLICATION**

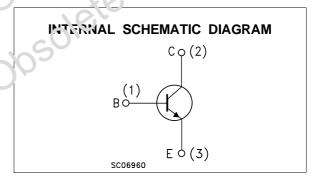
- SWITCHING REGULATORS
- MOTOR CONTROL
- HIGH FREQUENCY AND EFFICENCY CONVERTERS



The BUW48 and BUW49 are Multi-Epitaxial Planar NPN transistor in TO-218 plastic package.

They are intented for use in high frequency and efficiency converters such us motor controllers and industrial equipment.





#### **ABSOLUTE MAXINUM RATINGS**

Symbol	Parameter	Value		Unit	
		BUW48	BUW49		
VCEV	Collector-Emitter Voltage (V <sub>BE</sub> = -1.5 V)	120	160	V	
CEO	Collector-Emitter Voltage (I <sub>B</sub> = 0)	60	80	V	
V <sub>EBO</sub>	Emitter-Base Voltage (I <sub>C</sub> = 0)		7	V	
Ic	Collector Current	30		Α	
I <sub>CM</sub>	Collector Peak Current (t <sub>p</sub> < 5 ms)	45	40	А	
$I_{B}$	Base Current	8	6	А	
I <sub>BM</sub>	Base Peak Current (t <sub>p</sub> < 5 ms)	12	10	А	
Ptot	Total Dissipation at T <sub>c</sub> = 25 °C	150		W	
T <sub>stg</sub>	Storage Temperature	-65 to 175		°C	
Tj	Max. Operating Junction Temperature	1	°C		

October 2003 1/4

#### THERMAL DATA

R <sub>thj-case</sub>	Thermal Resistance Junction-case	Max	1	°C/W	
-----------------------	----------------------------------	-----	---	------	--

### **ELECTRICAL CHARACTERISTICS** (T<sub>case</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I <sub>CEX</sub>	Collector Cut-off Current (V <sub>BE</sub> = -1.5V	$V_{CE} = V_{CEX}$			1 3	mA mA
I <sub>EBO</sub>	Emitter Cut-off Current (I <sub>C</sub> = 0)	V <sub>EB</sub> = 5 V			1	mA
V <sub>CEO(sus)*</sub>	Collector-Emitter Sustaining Voltage (I <sub>B</sub> = 0)	I <sub>C</sub> = 0.2A L = 25 mH for <b>BUW48</b> for <b>BUW49</b>	60 80		داه	V
V <sub>EBO</sub>	Emitter-base Voltage (I <sub>C</sub> = 0)	I <sub>E</sub> = 50 mA	7	77,	CI	V
VCE(sat)*	Collector-Emitter Saturation Voltage	$\begin{array}{llllllllllllllllllllllllllllllllllll$	Pr	O <sub>O'</sub>	0.6 1.4 0.5 1.2	V V V
$V_{BE(sat)^*}$	Base-Emitter Saturation Voltage	$I_C = 40A$ $I_B = 4A$ for BUV.42 $I_C = 30A$ $I_B = 3A$ for BUV.42		09/	2.1 2	V
f <sub>T</sub>	Transition Frequency	I <sub>C</sub> = 1A	01	8		MHz

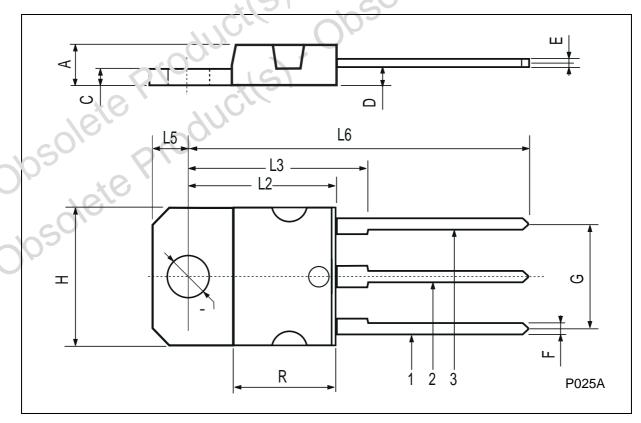
#### RESISTIVE LOAD

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
ton	Turn-on Time	for Buv 43		1.2	1.5	μs
ts	Storage Time	$V_{CC} = 60V$ $I_{C} = 40A$		0.6	1.1	μs
t <sub>f</sub>	Fall Time	$I_{51} = -I_{B2} = 4A$		0.17	0.25	μs
ts	Storage Time	for BUW48				
t <sub>f</sub>	Fall Time	$V_{CC} = 60V$ $I_C = 40A$			1.65	μs
	010	$I_{B1} = -I_{B2} = 4A$ $T_{C} = 100^{\circ}C$			0.5	μs
t <sub>on</sub>	Turn-on Time	for BUW49		0.8	1.2	μs
ts	Sinage Time	$V_{CC} = 80V$ $I_C = 30A$		0.6	1.1	μs
t <sub>f</sub>	f الد Time	$I_{B1} = -I_{B2} = 4A$		0.15	0.25	μs
ts	Storage Time	for BUW49				
1	Fall Time	$V_{CC} = 80V$ $I_C = 30A$			1.65	μs
P		$I_{B1} = -I_{B2} = 4$ $T_{C} = 100^{\circ}C$			0.5	μs
* Pulsed: Pulse	e duration = 300 μs, duty cycle <	1.5 %	1			
c0\						
02						

2/4

# TO-218 (SOT-93) MECHANICAL DATA

DIM.	mm			inch			
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.7		4.9	0.185		0.193	
С	1.17		1.37	0.046		0.054	
D		2.5			0.098		
Е	0.5		0.78	0.019		0.036	
F	1.1		1.3	0.043		ე.051	
G	10.8		11.1	0.425	AU	0.437	
Н	14.7		15.2	0.578	~100°	0.598	
L2	_		16.2	-		0.637	
L3		18		10/0	0.708		
L5	3.95		4.15	0.155	-400h	0.163	
L6		31			1.220		
R	_		2.2	-40		0.480	
Ø	4		4.1	0.157		0.161	



**▲7/** 3/4

homation functions of surparted by the production of surparted by the surparted by the production of surparted by the surparted by t

of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics.

All other names are the property of their respective owners.

© 2003 STMicroelectronics - All Rights reserved STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

http://www.st.com

47/ 4/4